

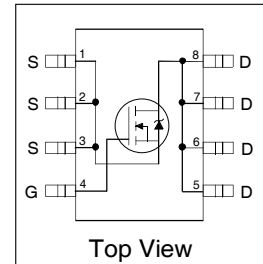


# THE DATASHEET OF IRF7811AVTRPBF-1



HEXFET® Power MOSFET

$V_{DS}$	<b>30</b>	<b>V</b>
$R_{DS(on) max}$ (@ $V_{GS} = 4.5V$ )	<b>14</b>	<b>mΩ</b>
$Q_g$ (typical)	<b>17</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>10.8</b>	<b>A</b>



**Features**

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



**Benefits**

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7811AVPbF-1	SO-8	Tube/Bulk	95	IRF7811AVPbF-1
		Tape and Reel	4000	IRF7811AVTRPbF-1

**Absolute Maximum Ratings**

Parameter	Symbol	IRF7811AV	Units
Drain-to-Source Voltage	$V_{DS}$	30	V
Gate-to-Source Voltage	$V_{GS}$	±20	
Continuous Output Current ( $V_{GS} \geq 4.5V$ )	$T_A = 25^\circ C$	10.8	A
	$T_L = 90^\circ C$	11.8	
Pulsed Drain Current ①	$I_{DM}$	100	
Power Dissipation ③	$T_A = 25^\circ C$	2.5	W
	$T_L = 90^\circ C$	3.0	
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C
Continuous Source Current (Body Diode)	$I_S$	2.5	A
Pulsed Source Current ①	$I_{SM}$	50	

**Thermal Resistance**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ③⑥	$R_{\theta JA}$	---	50	°C/W
Maximum Junction-to-Lead ⑥	$R_{\theta JL}$	---	20	

**Electrical Characteristics**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	—	11	14	m $\Omega$	$V_{GS} = 4.5V, I_D = 15A$ ②
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Drain-to-Source Leakage Current	$I_{DSS}$	—	—	50	$\mu A$	$V_{DS} = 30V, V_{GS} = 0V$
		—	—	20	$\mu A$	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100	mA	$V_{DS} = 24V, V_{GS} = 0V, T_J = 100^\circ C$
Gate-to-Source Leakage Current	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20V$
Total Gate Charge, Control FET	$Q_g$	—	17	26	nC	$V_{DS} = 24V, I_D = 15A, V_{GS} = 5.0V$
Total Gate Charge, Synch FET	$Q_g$	—	14	21	nC	$V_{GS} = 5.0V, V_{DS} < 100mV$
Pre-V <sub>th</sub> Gate-to-Source Charge	$Q_{gs1}$	—	3.4	—		$V_{DS} = 16V, I_D = 15A$
Post-V <sub>th</sub> Gate-to-Source Charge	$Q_{gs2}$	—	1.6	—		
Gate-to-Drain ("Miller") Charge	$Q_{gd}$	—	5.1	—		
Switch Charge ( $Q_{gs2} + Q_{gd}$ )	$Q_{SW}$	—	6.7	—		
Output Charge	$Q_{OSS}$	—	8.1	12		
Gate Resistance	$R_G$	0.5	—	4.4	$\Omega$	
Turn-On Delay Time	$t_{d(on)}$	—	8.6	—	ns	$V_{DD} = 16V$
Rise Time	$t_r$	—	21	—		$I_D = 15A$
Turn-Off Delay Time	$t_{d(off)}$	—	43	—		$V_{GS} = 5.0V$
Fall Time	$t_f$	—	10	—		Clamped Inductive Load
Input Capacitance	$C_{iss}$	—	1801	—	pF	$V_{GS} = 0V$
Output Capacitance	$C_{oss}$	—	723	—		$V_{DS} = 10V$
Reverse Transfer Capacitance	$C_{rss}$	—	46	—		

**Diode Characteristics**

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Diode Forward Voltage	$V_{SD}$	—	—	1.3	V	$T_J = 25^\circ C, I_S = 15A$ ②, $V_{GS} = 0V$
Reverse Recovery Charge ④	$Q_{rr}$	—	50	—	nC	$di/dt = 700A/\mu s$ $V_{DD} = 16V, V_{GS} = 0V, I_D = 15A$
Reverse Recovery Charge (with Parallel Schottsky) ④	$Q_{rr}$	—	43	—	nC	$di/dt = 700A/\mu s$ , (with 10BQ040) $V_{DD} = 16V, V_{GS} = 0V, I_D = 15A$

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width  $\leq 400 \mu s$ ; duty cycle  $\leq 2\%$ .
- ③ When mounted on 1 inch square copper board,  $t < 10$  sec.
- ④ Typ = measured -  $Q_{OSS}$
- ⑤ Typical values of  $R_{DS(on)}$  measured at  $V_{GS} = 4.5V$ ,  $Q_G$ ,  $Q_{SW}$  and  $Q_{OSS}$  measured at  $V_{GS} = 5.0V$ ,  $I_F = 15A$ .
- ⑥  $R_{\theta}$  is measured at  $T_J$  approximately  $90^\circ C$

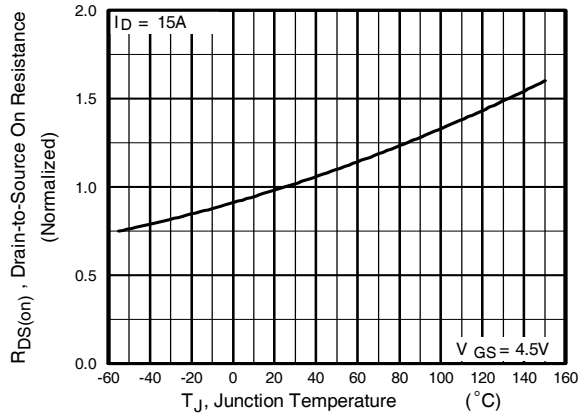


Figure 1. Normalized On-Resistance vs. Temperature

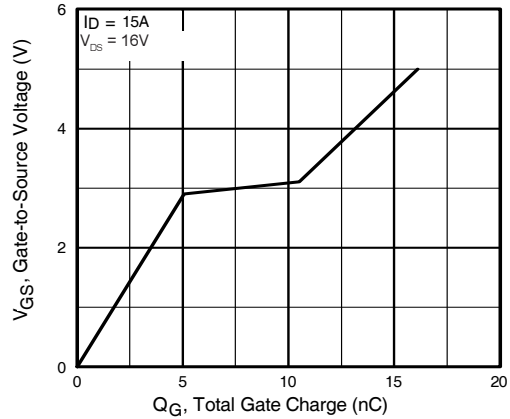


Figure 2. Gate-to-Source Voltage vs. Typical Gate Charge

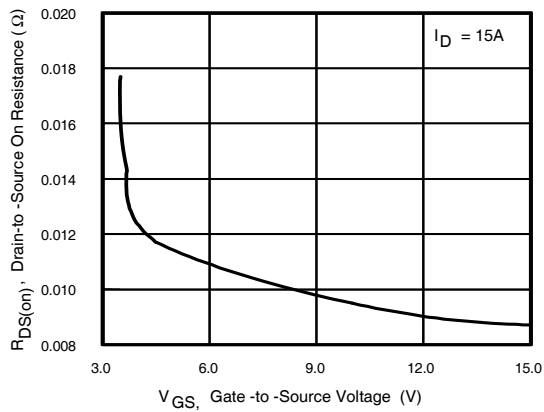
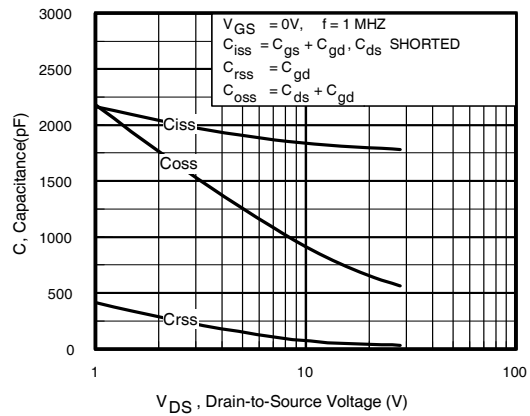

 Figure 3. Typical  $R_{DS(on)}$  vs. Gate-to-Source Voltage


Figure 4. Typical Capacitance vs. Drain-to-Source Voltage

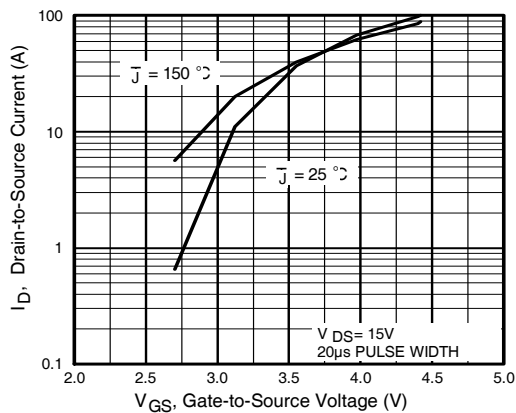


Figure 5. Typical Transfer Characteristics

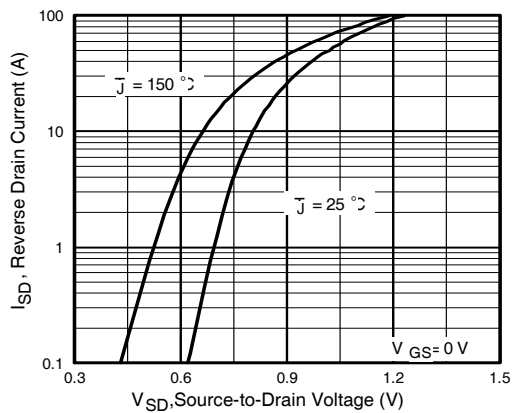


Figure 6. Typical Source-Drain Diode Forward Voltage

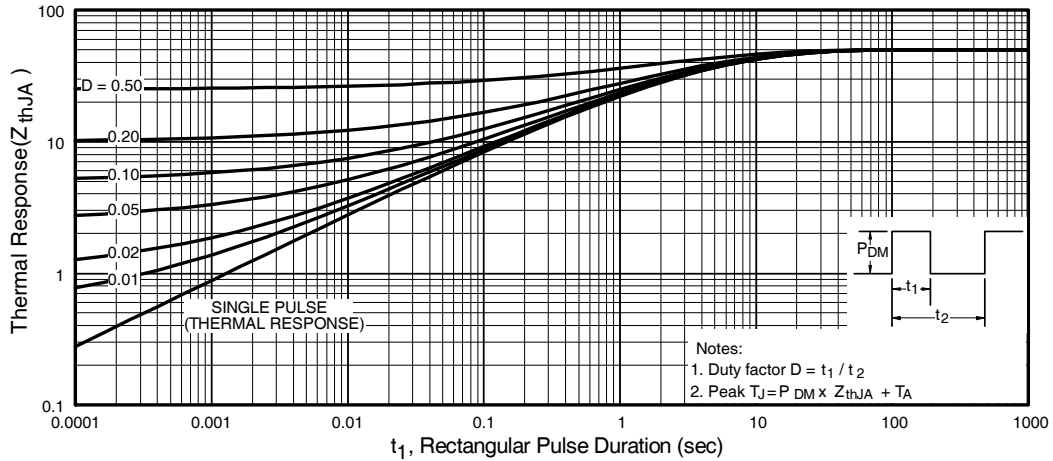


Figure 7. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

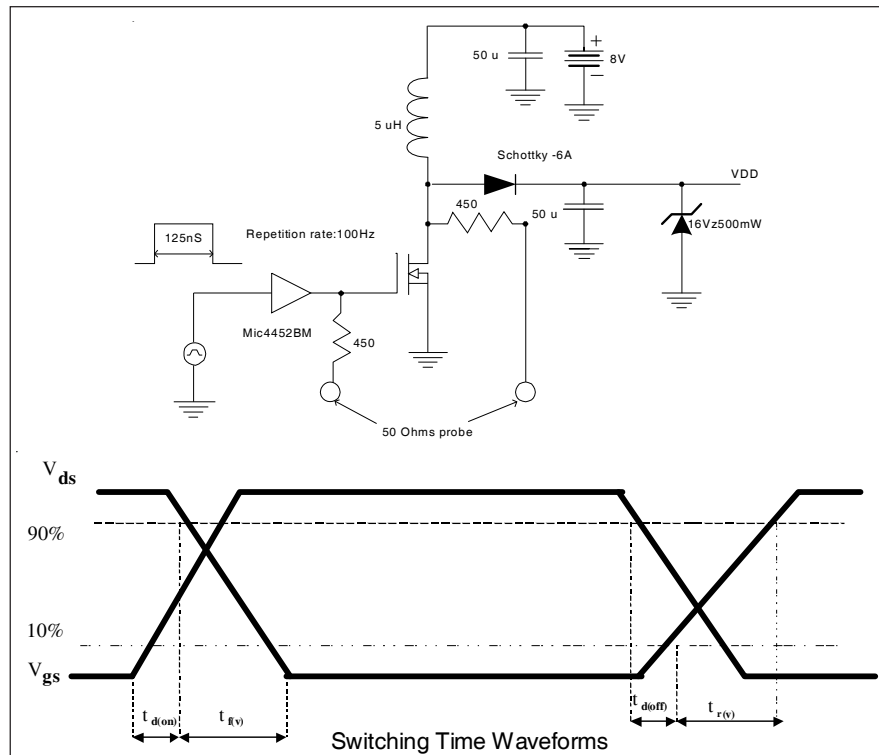
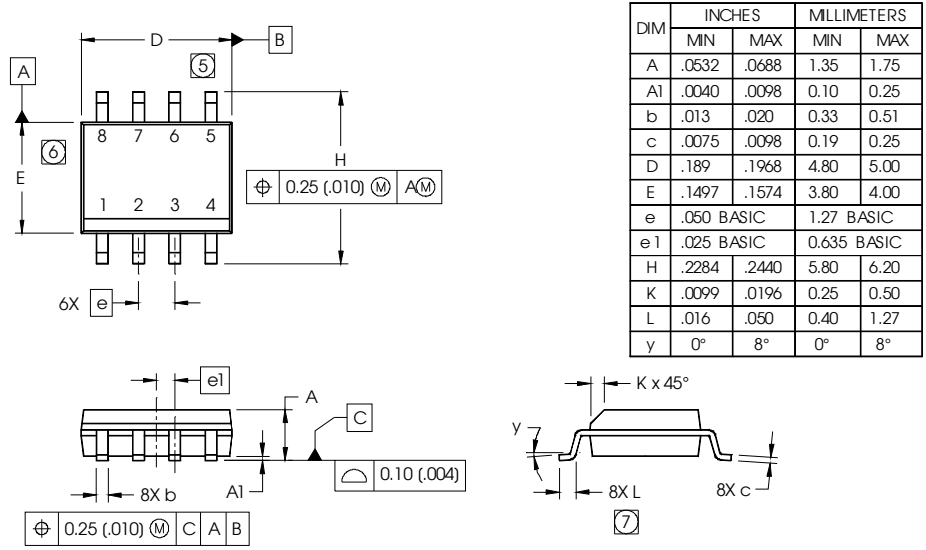


Figure 8. Clamped Inductive load test diagram and switching waveform



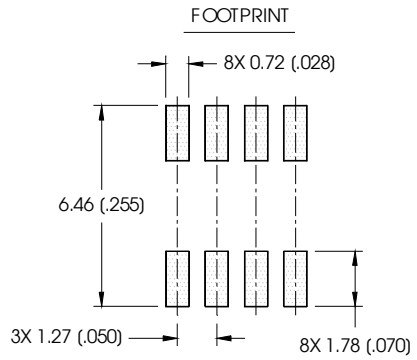
### SO-8 Package Outline

Dimensions are shown in millimeters (inches)



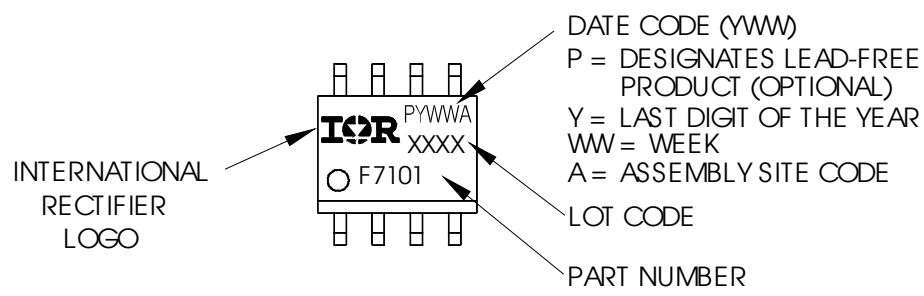
**NOTES:**

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



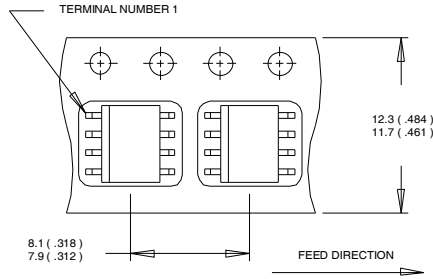
### SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)

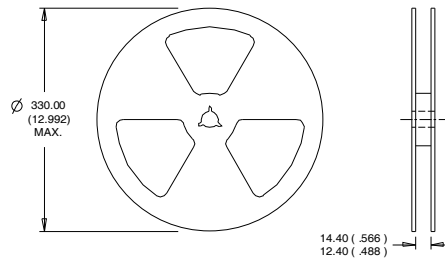


Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**SO-8 Tape and Reel**



- NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).  
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:  
 1. CONTROLLING DIMENSION : MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**Qualification information<sup>†</sup>**

Qualification level	Industriid (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>  
<sup>††</sup> Applicable version of JEDEC standard at the time of product release

## Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

 [View IRF7811AVTRPBF-1 on WIN SOURCE](#)

 [Infineon Technologies](#) Information

## Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management